## 1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a CFP15 (SOT1289) power and flat lead Surface-Mounted Device (SMD) plastic package.

#### 2. Features and benefits

- Average forward current: I<sub>F(AV)</sub> ≤ 15 A
- Reverse voltage: V<sub>R</sub> ≤ 50 V
- Extremely low forward voltage
- · High power capability due to clip-bonding technology and heat sink
- Small and thin SMD power plastic package, typical height 0.78 mm
- AEC-Q101 qualified

## 3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Freewheeling application
- Reverse polarity protection
- Low power consumption application

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5; f = 20 kHz; $T_{sp} \le$ 160 °C; square wave	-	-	15	A
$V_R$	reverse voltage	T <sub>j</sub> = 25 °C	-	-	50	V
V <sub>F</sub>	forward voltage	$I_F$ = 15 A; $t_p \le 300 \mu s$ ; δ ≤ 0.02; $T_j$ = 25 °C; pulsed	-	450	500	mV
I <sub>R</sub>	reverse current	$V_R$ = 10 V; $t_p \le 3$ ms; $\delta \le 0.3$ ; $T_j$ = 25 °C; pulsed	-	30	70	μA
		$V_R = 50 \text{ V; } t_p \le 3 \text{ ms; } \delta \le 0.3;$ $T_j = 25 \text{ °C; pulsed}$	-	260	1000	μA





## 5. Pinning information

#### Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Α	anode		K PA
2	Α	anode	3	aaa-009063
3	K	cathode	2 CFP15 (SOT1289)	

# 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMEG050V150EPD	CFP15	plastic, thermal enhanced ultra thin SMD package; 3 leads; body: 5.8 x 4.3 x 0.78 mm	SOT1289

# 7. Marking

Table 4. Marking codes

Type number	Marking code
PMEG050V150EPD	050V 150E

# 8. Limiting values

## Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>R</sub>	reverse voltage	T <sub>j</sub> = 25 °C		-	50	V
I <sub>F</sub>	forward current	T <sub>sp</sub> = 155 °C; δ = 1		-	21	Α
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5; f = 20 kHz; $T_{sp} \le$ 160 °C; square wave		-	15	A
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	240	A
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	1.66	W
			[2]	-	2.15	W
			[3]	-	3.75	W
Tj	junction temperature			-	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C

PMEG050V150EPD

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Symbol	Parameter	Conditions	Min	Max	Unit
T <sub>stg</sub>	storage temperature		-65	175	°C

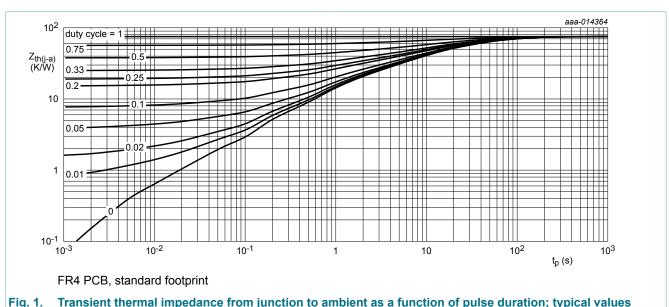
- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.
- [3] Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.

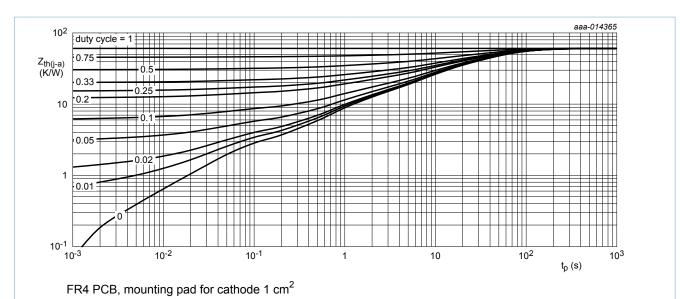
## 9. Thermal characteristics

Table 6. Thermal characteristics

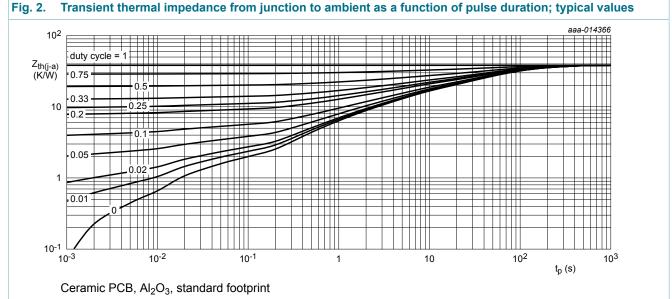
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance from junction to ambient	thermal resistance	in free air	[1][2]	-	-	90	K/W
		[1][3]	-	-	70	K/W	
	ambient		[1][4]	-	-	40	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		<u>[5]</u>	-	-	3	K/W

- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P<sub>R</sub> are a significant part of the total power losses.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.
- [4] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [5] Soldering point of cathode tab.





Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

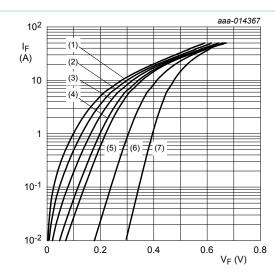


Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig. 3.

## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
$V_{(BR)R}$	reverse breakdown voltage	$I_R = 5 \text{ mA}; T_j = 25 \text{ °C}; t_p \le 1.2 \text{ ms};$ $\delta \le 0.12; \text{ pulsed}$	50	-	-	V	
V <sub>F</sub>	forward voltage	$I_F$ = 1 A; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_j$ = 25 °C; pulsed	-	305	350	mV	
		$I_F$ = 5 A; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_j$ = 25 °C; pulsed	-	365	420	mV	
		$I_F$ = 10 A; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_j$ = 25 °C; pulsed	-	415	-	mV	
		$I_F$ = 15 A; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_j$ = 25 °C; pulsed	-	450	500	mV	
		$I_F$ = 15 A; $t_p \le 300$ μs; $δ \le 0.02$ ; $T_j$ = 125 °C; pulsed	-	380	-	mV	
I <sub>R</sub> reverse	reverse current	$V_R$ = 5 V; $t_p$ ≤ 3 ms; $\delta$ ≤ 0.3; $T_j$ = 25 °C; pulsed	-	20	-	μA	
			$V_R$ = 10 V; $t_p \le 3$ ms; $\delta \le 0.3$ ; $T_j$ = 25 °C; pulsed	-	30	70	μA
		$V_R$ = 30 V; $t_p \le 3$ ms; $\delta \le 0.3$ ; $T_j$ = 25 °C; pulsed	-	70	-	μA	
		$V_R = 50 \text{ V}; t_p \le 3 \text{ ms}; \delta \le 0.3;$ $T_j = 25 \text{ °C}; \text{ pulsed}$	-	260	1000	μA	
C <sub>d</sub>	diode capacitance	V <sub>R</sub> = 1 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	1750	-	pF	
		V <sub>R</sub> = 10 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	570	-	pF	
t <sub>rr</sub>	reverse recovery time step recovery	$I_F = 0.5 \text{ A}$ ; $I_R = 0.5 \text{ A}$ ; $I_{R(meas)} = 0.1 \text{ A}$ ; $I_{j} = 25 \text{ °C}$	-	51	-	ns	
t <sub>rr</sub>	reverse recovery time ramp recovery	$dI_F/dt = 200 \text{ A/}\mu\text{s}; T_j = 25 \text{ °C}; I_F = 6 \text{ A};$ $V_R = 26 \text{ V}$	-	20	-	ns	
$V_{FRM}$	peak forward recovery voltage	$I_F = 0.5 \text{ A}; dI_F/dt = 20 \text{ A/}\mu\text{s}; T_j = 25 ^{\circ}\text{C}$	-	288	-	mV	



pulsed condition

(1)  $T_i = 175 \, ^{\circ}C$ 

(2)  $T_i = 150 \, ^{\circ}C$ 

(3)  $T_i = 125 \, ^{\circ}C$ 

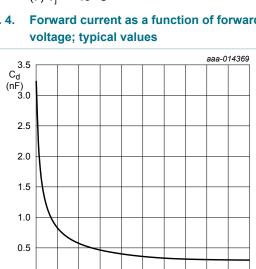
(4)  $T_i = 100 \, ^{\circ}C$ 

 $(5) T_i = 85 °C$ 

(6)  $T_i = 25 \,^{\circ}C$ 

 $(7) T_i = -40 °C$ 

Forward current as a function of forward Fig. 4.



 $f = 1 MHz; T_{amb} = 25 °C$ 

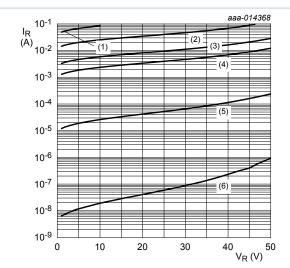
Fig. 6. Diode capacitance as a function of reverse voltage; typical values

20

30

50

V<sub>R</sub> (V)



pulsed condition

(1)  $T_i = 150 \, ^{\circ}C$ 

(2)  $T_i = 125 \, ^{\circ}C$ 

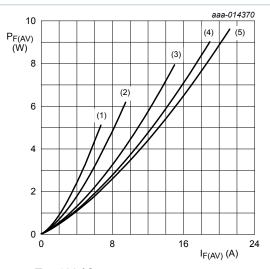
(3)  $T_i = 100 \, ^{\circ}C$ 

(4)  $T_i = 85 \, ^{\circ}C$ 

(5)  $T_i = 25 \, ^{\circ}C$ 

(6)  $T_i = -40 \, ^{\circ}C$ 

Fig. 5. Reverse current as a function of reverse voltage; typical values



T<sub>i</sub> = 100 °C

 $(1) \delta = 0.1$ 

 $(2) \delta = 0.2$ 

 $(3) \delta = 0.5$ 

 $(4) \delta = 0.8$ 

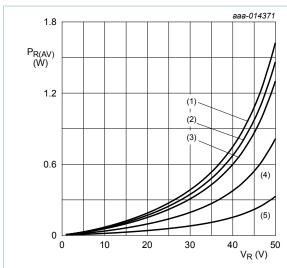
 $(5) \delta = 1$ 

Fig. 7. Average forward power dissipation as a function of average forward current; typical values

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 $T_i = 100 \, ^{\circ}C$ 

 $(1) \delta = 1$ 

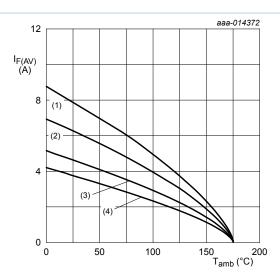
 $(2) \delta = 0.9$ 

 $(3) \delta = 0.8$ 

 $(4) \delta = 0.5$ 

 $(5) \delta = 0.2$ 

Fig. 8. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

T<sub>i</sub> = 175 °C

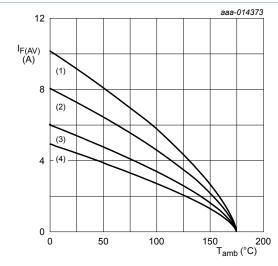
(1)  $\delta$  = 1; DC

(2)  $\delta$  = 0.5; f = 20 kHz

(3)  $\delta = 0.2$ ; f = 20 kHz

(4)  $\delta = 0.1$ ; f = 20 kHz

Fig. 9. Average forward current as a function of ambient temperature; typical values



FR4 PCB, mounting pad for cathode 1 cm<sup>2</sup>

T<sub>i</sub> = 175 °C

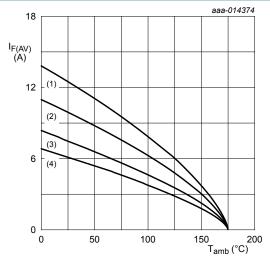
(1)  $\delta$  = 1; DC

(2)  $\delta = 0.5$ ; f = 20 kHz

(3)  $\delta = 0.2$ ; f = 20 kHz

(4)  $\delta = 0.1$ ; f = 20 kHz

Fig. 10. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint

T<sub>i</sub> = 175 °C

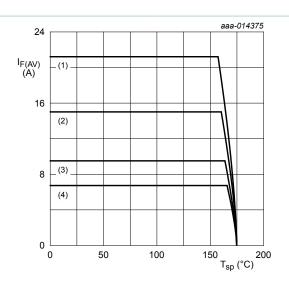
(1)  $\delta$  = 1; DC

(2)  $\delta$  = 0.5; f = 20 kHz

(3)  $\delta$  = 0.2; f = 20 kHz

(4)  $\delta = 0.1$ ; f = 20 kHz

Fig. 11. Average forward current as a function of ambient temperature; typical values



T<sub>i</sub> = 175 °C

(1)  $\delta$  = 1; DC

(2)  $\delta$  = 0.5; f = 20 kHz

(3)  $\delta$  = 0.2; f = 20 kHz

(4)  $\delta$  = 0.1; f = 20 kHz

Fig. 12. Average forward current as a function of solder point temperature; typical values

## 11. Test information

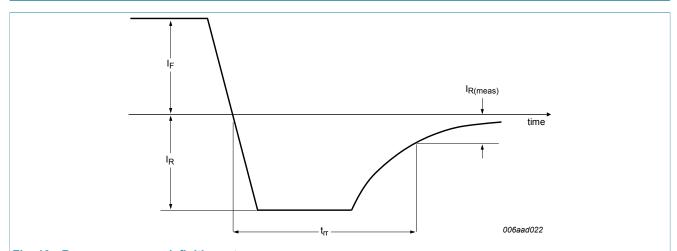


Fig. 13. Reverse recovery definition; step recovery

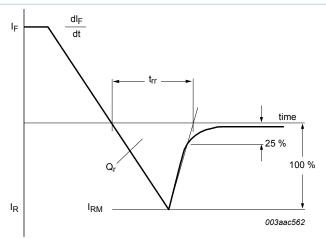


Fig. 14. Reverse recovery definition; ramp recovery

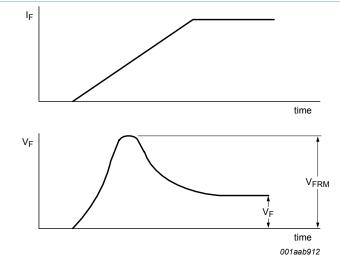
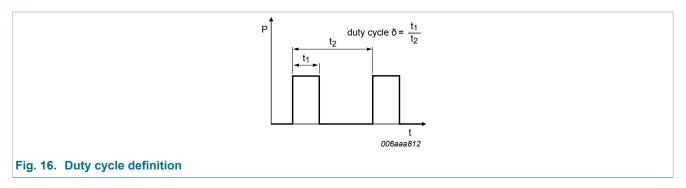


Fig. 15. Forward recovery definition

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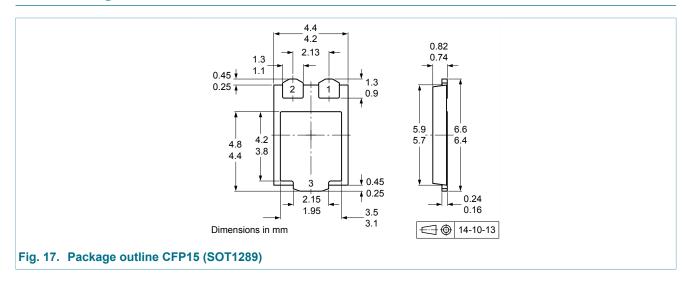


The current ratings for the typical waveforms are calculated according to the equations:  $I_{F(AV)} = I_M \times \delta$  with  $I_M$  defined as peak current,  $I_{RMS} = I_{F(AV)}$  at DC, and  $I_{RMS} = I_M \times \sqrt{\delta}$  with  $I_{RMS}$  defined as RMS current.

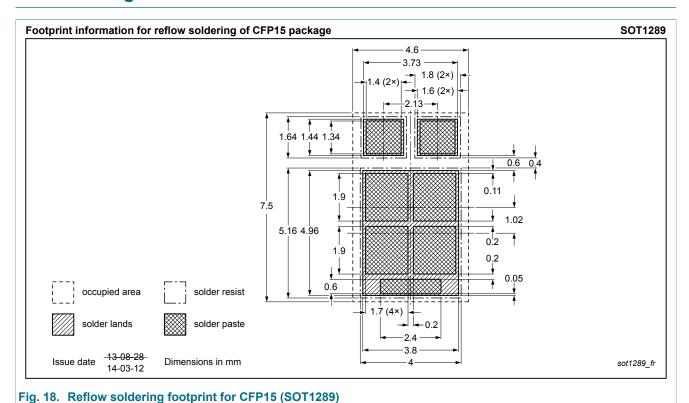
## 11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

## 12. Package outline



## 13. Soldering



# 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMEG050V150EPD v.3	20141204	Product data sheet	-	PMEG050V150EPD v.2
Modifications:	<ul> <li>Product status c</li> </ul>	hanged		
PMEG050V150EPD v.2	20140704	Preliminary data sheet	-	PMEG050V150EPD v.1
PMEG050V150EPD v.1	20140519	Objective data sheet	-	-

## 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <a href="http://www.nxp.com">http://www.nxp.com</a>.

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